

The RF Sub-Micron MOSFET Line

RF Power Field Effect Transistors

N-Channel Enhancement-Mode Lateral MOSFETs

Designed for digital and analog cellular PCN and PCS base station applications with frequencies from 1000 to 2500 MHz. Characterized for operation Class A and Class AB at 26 volts in commercial and industrial applications.

- Specified Two-Tone Performance @ 1930 and 2000 MHz, 26 Volts
Output Power — 4 Watts PEP
Power Gain — 11 dB
Efficiency — 30%
Intermodulation Distortion — -29 dBc
- Capable of Handling 10:1 VSWR, @ 26 Vdc,
2000 MHz, 4 Watts CW Output Power
- Excellent Thermal Stability
- Characterized with Series Equivalent Large-Signal Impedance Parameters
- S-Parameter Characterization at High Bias Levels
- Available in Tape and Reel. R1 Suffix = 500 Units per
12 mm, 7 inch Reel.

MRF281SR1
MRF281ZR1

2000 MHz, 4 W, 26 V
LATERAL N-CHANNEL
BROADBAND
RF POWER MOSFETs



CASE 458B-03, STYLE 1
(NI-200S)
(MRF281SR1)



CASE 458C-03, STYLE 1
(NI-200Z)
(MRF281ZR1)

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	65	Vdc
Gate-Source Voltage	V_{GS}	± 20	Vdc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	20 0.115	Watts W/ $^\circ\text{C}$
Storage Temperature Range	T_{stg}	-65 to +150	$^\circ\text{C}$
Operating Junction Temperature	T_J	200	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	5.74	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

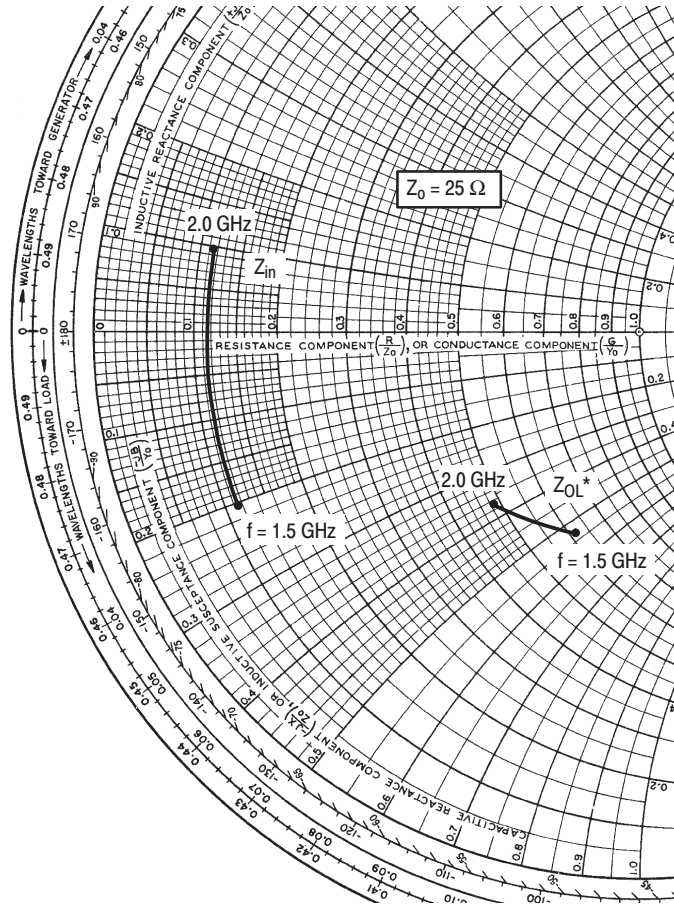
Drain-Source Breakdown Voltage ($V_{GS} = 0$, $I_D = 10 \mu\text{Adc}$)	$V_{(BR)DS}$	65	74	—	Vdc
Zero Gate Voltage Drain Current ($V_{DS} = 28 \text{ Vdc}$, $V_{GS} = 0$)	I_{DSS}	—	—	10	μAdc
Gate-Source Leakage Current ($V_{GS} = 20 \text{ Vdc}$, $V_{DS} = 0$)	I_{GSS}	—	—	1	μAdc

NOTE – CAUTION – MOS devices are susceptible to damage from electrostatic charge. Reasonable precautions in handling and packaging MOS devices should be observed.



ELECTRICAL CHARACTERISTICS continued ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
ON CHARACTERISTICS					
Gate Threshold Voltage ($V_{DS} = 10\text{ Vdc}$, $I_D = 20\text{ }\mu\text{Adc}$)	$V_{GS(th)}$	2.4	3.2	4	Vdc
Gate Quiescent Voltage ($V_{DS} = 26\text{ Vdc}$, $I_D = 25\text{ mAdc}$)	$V_{GS(q)}$	3	4.1	5	Vdc
Drain–Source On–Voltage ($V_{GS} = 10\text{ Vdc}$, $I_D = 0.1\text{ A}$)	$V_{DS(on)}$	0.18	0.24	0.30	Vdc
DYNAMIC CHARACTERISTICS					
Input Capacitance ($V_{DS} = 26\text{ Vdc}$, $V_{GS} = 0$, $f = 1.0\text{ MHz}$)	C_{iss}	—	5.5	—	pF
Output Capacitance ($V_{DS} = 26\text{ Vdc}$, $V_{GS} = 0$, $f = 1.0\text{ MHz}$)	C_{oss}	—	3.3	—	pF
Reverse Transfer Capacitance ($V_{DS} = 26\text{ Vdc}$, $V_{GS} = 0$, $f = 1.0\text{ MHz}$)	C_{rss}	—	0.17	—	pF
FUNCTIONAL TESTS (In Motorola Test Fixture)					
Common–Source Amplifier Power Gain ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 4\text{ W PEP}$, $I_{DQ} = 25\text{ mA}$, $f_1 = 2000.0\text{ MHz}$, $f_2 = 2000.1\text{ MHz}$)	G_{ps}	11	12.5	—	dB
Drain Efficiency ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 4\text{ W PEP}$, $I_{DQ} = 25\text{ mA}$, $f_1 = 2000.0\text{ MHz}$, $f_2 = 2000.1\text{ MHz}$)	η	30	33	—	%
Input Return Loss ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 4\text{ W PEP}$, $I_{DQ} = 25\text{ mA}$, $f_1 = 2000.0\text{ MHz}$, $f_2 = 2000.1\text{ MHz}$)	IRL	—	–16	–10	dB
Intermodulation Distortion ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 4\text{ W PEP}$, $I_{DQ} = 25\text{ mA}$, $f_1 = 2000.0\text{ MHz}$, $f_2 = 2000.1\text{ MHz}$)	IMD	—	–31	–29	dBc
Common–Source Amplifier Power Gain ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 4\text{ W PEP}$, $I_{DQ} = 25\text{ mA}$, $f_1 = 1930.0\text{ MHz}$, $f_2 = 1930.1\text{ MHz}$)	G_{ps}	11	12.5	—	dB
Drain Efficiency ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 4\text{ W}$, $I_{DQ} = 25\text{ mA}$, $f_1 = 1930.0\text{ MHz}$, $f_2 = 1930.1\text{ MHz}$)	η	30	—	—	%
Input Return Loss ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 4\text{ W PEP}$, $I_{DQ} = 25\text{ mA}$, $f_1 = 1930.0\text{ MHz}$, $f_2 = 1930.1\text{ MHz}$)	IRL	—	–16	–10	dB
Intermodulation Distortion ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 4\text{ W PEP}$, $I_{DQ} = 25\text{ mA}$, $f_1 = 1930.0\text{ MHz}$, $f_2 = 1930.1\text{ MHz}$)	IMD	—	–31	—	dBc
Common–Source Amplifier Power Gain ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 4\text{ W CW}$, $I_{DQ} = 25\text{ mA}$, $f_1 = 2000.0\text{ MHz}$)	G_{ps}	10.5	12	—	dB
Drain Efficiency ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 4\text{ W CW}$, $I_{DQ} = 25\text{ mA}$, $f_1 = 2000.0\text{ MHz}$)	η	40	44	—	%
Output Mismatch Stress ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 4\text{ W CW}$, $I_{DQ} = 25\text{ mA}$, $f_1 = 2000.0\text{ MHz}$, VSWR = 10:1, All Phase Angles at Frequency of Test)	Ψ	No Degradation In Output Power			



$V_{DD} = 26 \text{ V}$, $I_{DQ} = 25 \text{ mA}$, $P_{out} = 4 \text{ W (PEP)}$

f MHz	Z_{in} Ω	Z_{OL}^* Ω
1500	$3.15 - j5.3$	$15.5 - j13.6$
1600	$3.1 - j3.8$	$14.7 - j12.5$
1700	$3.1 - j2.3$	$14.0 - j11.7$
1800	$3.1 - j0.7$	$13.4 - j11.0$
1900	$3.1 + j0.9$	$12.8 - j10.1$
2000	$3.1 + j2.4$	$12.2 - j9.2$

Z_{in} = Complex conjugate of source impedance.

Z_{OL}^* = Complex conjugate of the optimum load impedance at given output power, voltage, IMD, bias current and frequency.

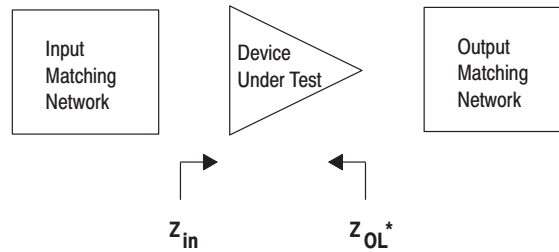


Figure 1. Series Equivalent Input and Output Impedance

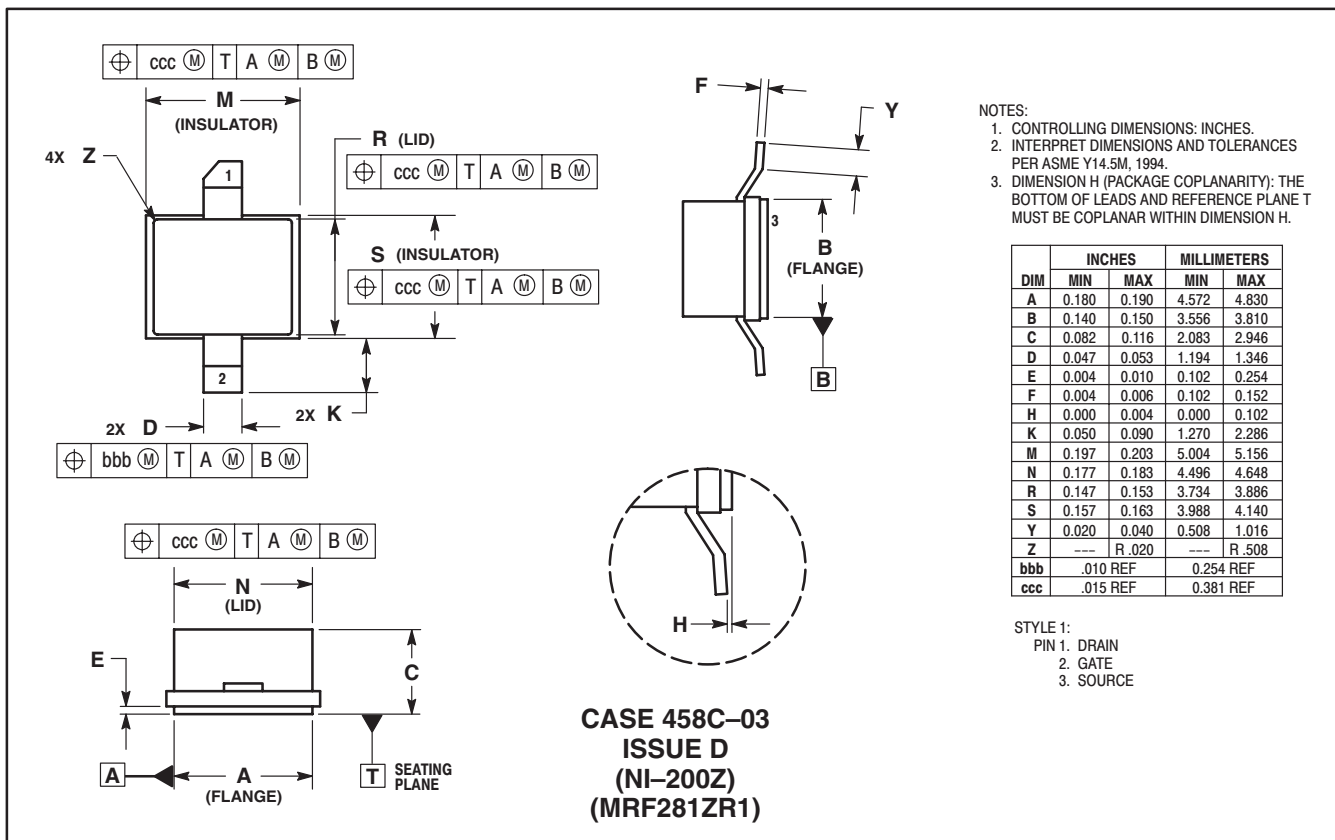
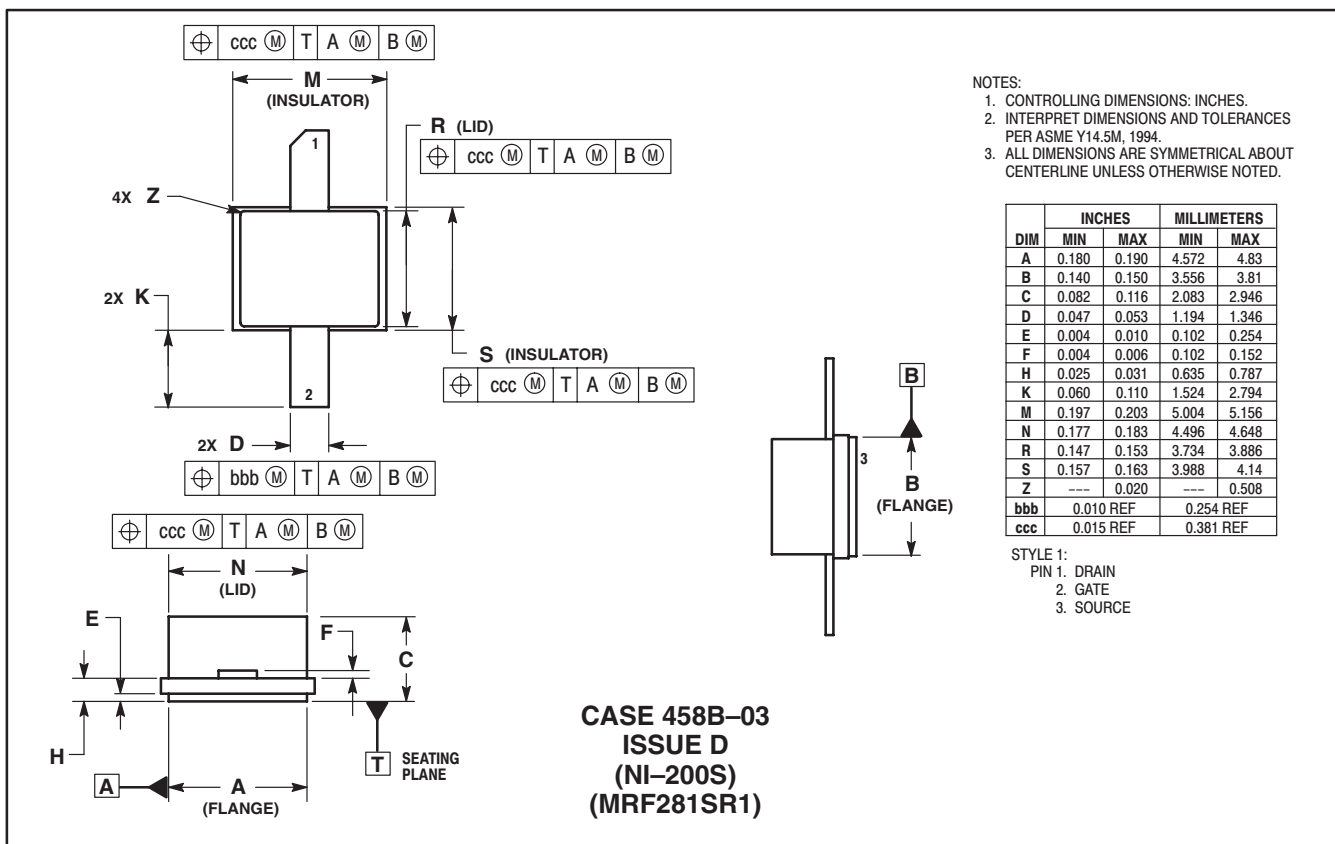
Table 1. Common Source S-Parameters at $V_{DS} = 26$ Vdc, $I_D = 250$ mAdc

f GHz	S ₁₁		S ₂₁		S ₁₂		S ₂₂	
	S ₁₁	∠ φ	dB	∠ φ	S ₁₂	∠ φ	S ₂₂	∠ φ
0.1	.982	-28	18.9	160	.008	73	.851	-13
0.2	.947	-52	17.0	143	.015	58	.811	-25
0.3	.912	-73	15.0	129	.019	45	.770	-33
0.4	.886	-90	12.9	117	.022	36	.741	-42
0.5	.859	-103	11.1	108	.022	28	.719	-47
0.6	.854	-114	9.69	100	.023	23	.718	-51
0.7	.841	-123	8.54	93	.022	18	.709	-56
0.8	.837	-131	7.57	87	.021	15	.714	-59
0.9	.838	-138	6.69	81	.019	12	.719	-62
1.0	.841	-143	6.01	76	.018	11	.728	-64
1.1	.840	-149	5.41	72	.015	12	.742	-66
1.2	.849	-153	4.91	68	.013	13	.745	-68
1.3	.848	-158	4.51	64	.012	18	.758	-69
1.4	.856	-162	4.12	60	.010	26	.769	-70
1.5	.858	-167	3.78	57	.009	36	.786	-70
1.6	.871	-170	3.50	54	.008	54	.797	-72
1.7	.868	-173	3.22	51	.009	69	.808	-71
1.8	.870	-176	3.00	49	.009	82	.823	-72
1.9	.872	-180	2.80	46	.011	95	.828	-72
2.0	.877	178	2.63	44	.013	104	.845	-72
2.1	.876	174	2.47	41	.015	109	.843	-72
2.2	.880	171	2.36	39	.018	111	.859	-71
2.3	.882	168	2.21	36	.021	114	.858	-72
2.4	.886	165	2.12	34	.024	114	.872	-70
2.5	.896	162	1.97	32	.027	115	.863	-70
2.6	.897	158	1.89	29	.029	117	.873	-69

NOTES

NOTES

PACKAGE DIMENSIONS



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